

A detailed cross-sectional view of a semiconductor device. A central vertical channel (1) is formed in a substrate (7). The channel is lined with a material (1a) and contains a central rod-like structure (4). The channel is surrounded by a layer (2) which has a central region (2b) and side regions (2c). The side regions (2c) are filled with a material (5) containing a hatched pattern. The entire structure is supported by a base (3) which is connected to ground (indicated by a symbol). A top layer (6) is shown above the channel, with a small opening (2a) in the side region (2c).

FIG. 2

